

Silicon PNP Darlington Power Transistor

2SB1502

DESCRIPTION

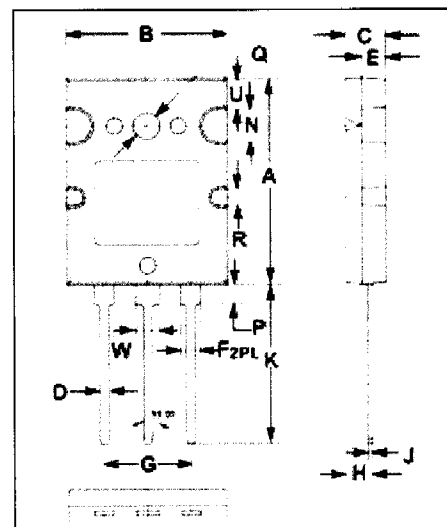
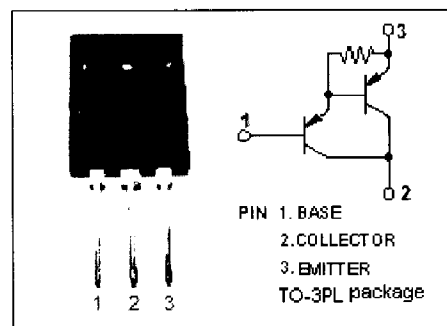
- High DC Current Gain-
 : $h_{FE} = 5000(\text{Min}) @ I_C = -4A$
- Low-Collector Saturation Voltage-
 : $V_{CE(\text{sat})} = -2.5V(\text{Max.}) @ I_C = -4A$
- Complement to Type 2SD2275

APPLICATIONS

- Designed for power amplifier applications
- Optimum for 55W HiFi output applications.

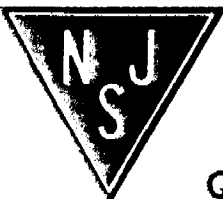
ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-8	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	60	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	3.5	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	25.50	26.50
B	19.80	20.20
C	4.50	5.50
D	0.90	1.10
E	2.80	3.20
F	2.40	2.60
G	10.80	11.00
H	3.10	3.30
J	0.50	0.70
K	20.00	21.00
N	3.90	4.10
P	2.40	2.60
Q	3.10	3.50
R	1.90	2.10
U	3.90	4.10
W	2.90	3.10

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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}; I_B = -4\text{mA}$			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -4\text{A}; I_B = -4\text{mA}$			-3.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}; I_E = 0$			-100	μA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -100\text{V}; I_B = 0$			-100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-100	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	2000			
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}; V_{CE} = -5\text{V}$	5000		30000	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}$		20		MHz

Switching Times

t_{on}	Turn-on Time	$I_C = -4\text{A}; I_{B1} = -I_{B2} = -4\text{mA}; V_{CC} = -50\text{V}$		1.0		μs
t_{stg}	Storage Time			0.8		μs
t_f	Fall Time			1.0		μs

► h_{FE-2} Classifications

Q	S	P
5000-15000	7000-21000	8000-30000